



DISCRETE POWER DIODES and THYRISTORS
DATA BOOK



ST700C..L SERIES

PHASE CONTROL THYRISTORS

Hockey Puk Version

Features

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case TO-200AC (B-PUK)

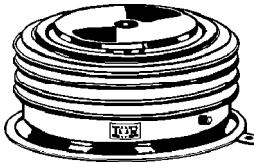
Typical Applications

- DC motor control
- Controlled DC power supplies
- AC controllers

Major Ratings and Characteristics

Parameters	ST700C..L	Units
$I_{T(AV)}$	910	A
@ T_{hs}	55	°C
$I_{T(RMS)}$	1857	A
@ T_{hs}	25	°C
I_{TSM}	15700	A
@ 50Hz	15700	A
@ 60Hz	16400	A
I^2t	1232	KA ² s
@ 50Hz	1125	KA ² s
V_{DRM}/V_{RRM}	1200 to 2200	V
t_q typical	150	μs
T_J	- 40 to 125	°C

910A



case style TO-200AC (B-PUK)

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ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{DRM}/V_{RRM} , max. repetitive peak and off-state voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. @ $T_J = T_J$ max mA
ST700C..L	12	1200	1300	80
	16	1600	1700	
	18	1800	1900	
	20	2000	2100	
	22	2200	2300	

On-state Conduction

Parameter	ST700C..L	Units	Conditions
$I_{T(AV)}$ Max. average on-state current @ Heatsink temperature	910 (355)	A	180° conduction, half sine wave double side (single side) cooled
	55 (85)	°C	
$I_{T(RMS)}$ Max. RMS on-state current	1857	A	DC @ 25°C heatsink temperature double side cooled
I_{TSM} Max. peak, one-cycle non-repetitive surge current	15700		$t = 10ms$
	16400		No voltage reapplied
	13200		$t = 10ms$
	13800		100% V_{RRM} reapplied
I^2t Maximum I^2t for fusing	1232	KA ² s	Sinusoidal half wave, Initial $T_J = T_J$ max.
	1125		$t = 8.3ms$
	871		$t = 10ms$
	795		100% V_{RRM} reapplied
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	12321	KA ² \sqrt{s}	$t = 0.1$ to 10ms, no voltage reapplied
$V_{T(TO)1}$ Low level value of threshold voltage	1.00	V	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ max.
$V_{T(TO)2}$ High level value of threshold voltage	1.13		$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ max.
r_{t1} Low level value of on-state slope resistance	0.40	mΩ	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ max.
r_{t2} High level value of on-state slope resistance	0.35		$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ max.
V_{TM} Max. on-state voltage	1.80	V	$I_{pk} = 2000A$, $T_J = T_J$ max, $t_p = 10ms$ sine pulse
I_H Maximum holding current	600	mA	$T_J = 25^\circ C$, anode supply 12V resistive load
I_L Typical latching current	1000		

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Switching

Parameter	ST700C..L	Units	Conditions
di/dt Max. non-repetitive rate of rise of turned-on current	1000	A/μs	Gate drive 20V, 20Ω, $t_r \leq 1\mu s$ $T_J = T_{J_{max}}$, anode voltage ≤ 80% V_{DRM}
t_d Typical delay time	1.0	μs	Gate current 1A, $di_g/dt = 1A/\mu s$ $V_d = 0.67\% V_{DRM}$, $T_J = 25^\circ C$
t_q Typical turn-off time	150		$I_{TM} = 750A$, $T_J = T_{J_{max}}$, $di/dt = 60A/\mu s$, $V_R = 50V$ $dv/dt = 20V/\mu s$, Gate 0V 100Ω, $t_p = 500\mu s$

Blocking

Parameter	ST700C..L	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/μs	$T_J = T_{J_{max}}$ linear to 80% rated V_{DRM}
I_{DRM} Max. peak reverse and off-state leakage current	80	mA	$T_J = T_{J_{max}}$, rated V_{DRM}/V_{RRM} applied

Triggering

Parameter	ST700C..L	Units	Conditions
P_{GM} Maximum peak gate power	10.0		$T_J = T_{J_{max}}$, $t_p \leq 5ms$
$P_{G(AV)}$ Maximum average gate power	2.0		$T_J = T_{J_{max}}$, $f = 50Hz$, $d\% = 50$
I_{GM} Max. peak positive gate current	3.0	A	$T_J = T_{J_{max}}$, $t_p \leq 5ms$
$+V_{GM}$ Maximum peak positive gate voltage	20		
$-V_{GM}$ Maximum peak negative gate voltage	5.0		$T_J = T_{J_{max}}$, $t_p \leq 5ms$
I_{GT} DC gate current required to trigger	TYP.	MAX.	
	200	-	$T_J = -40^\circ C$
	100	200	$T_J = 25^\circ C$
	50	-	$T_J = 125^\circ C$
V_{GT} DC gate voltage required to trigger	2.5	-	$T_J = -40^\circ C$
	1.8	3.0	$T_J = 25^\circ C$
	1.1	-	$T_J = 125^\circ C$
I_{GD} DC gate current not to trigger	10	mA	$T_J = T_{J_{max}}$
V_{GD} DC gate voltage not to trigger	0.25	V	

Max. required gate trigger/ current/voltage are the lowest value which will trigger all units 12V anode-to-cathode applied
 Max. gate current/voltage not to trigger is the max. value which will not trigger any unit with rated V_{DRM} anode-to-cathode applied

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Thermal and Mechanical Specification

Parameter	ST700C..L	Units	Conditions
T _J	Max. operating temperature range	-40 to 125	°C
T _{stg}	Max. storage temperature range	-40 to 150	
R _{thJ-hs}	Max. thermal resistance, junction to heatsink	0.073 0.031	K/W
R _{thC-hs}	Max. thermal resistance, case to heatsink	0.011 0.006	
F	Mounting force, ± 10%	14700 (1500)	N (Kg)
wt	Approximate weight	255	g
Case style	TO - 200AC (B-PUK)	See Outline Table	

ΔR_{thJ-hs} Conduction

(The following table shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction		Rectangular conduction		Units	Conditions
	Single Side	Double Side	Single Side	Double Side		
180°	0.009	0.009	0.006	0.006	K/W	T _J = T _J max.
120°	0.011	0.011	0.011	0.011		
90°	0.014	0.014	0.015	0.015		
60°	0.020	0.020	0.021	0.021		
30°	0.036	0.036	0.036	0.036		

Ordering Information Table

Device Code	ST	70	0	C	22	L	1	
	1	2	3	4	5	6	7	8
1	- Thyristor							
2	- Essential part number							
3	- 0 = Converter grade							
4	- C = Ceramic Puk							
5	- Voltage code: Code x 100 = V _{RRM} (See Voltage Rating Table)							
6	- L = Puk Case TO-200AC (B-PUK)							
7	- 0 = Eyelet terminals (Gate and Auxiliary Cathode Unsoldered Leads) 1 = Fast-on terminals (Gate and Auxiliary Cathode Unsoldered Leads) 2 = Eyelet terminals (Gate and Auxiliary Cathode Soldered Leads) 3 = Fast-on terminals (Gate and Auxiliary Cathode Soldered Leads)							
8	- Critical dv/dt: None = 500V/μsec (Standard selection) L = 1000V/μsec (Special selection)							

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Outline Table

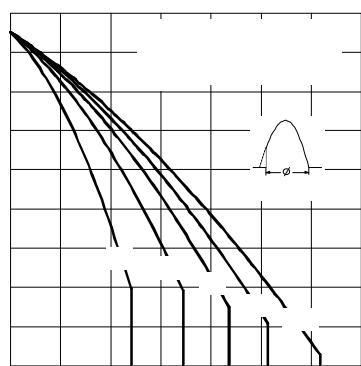
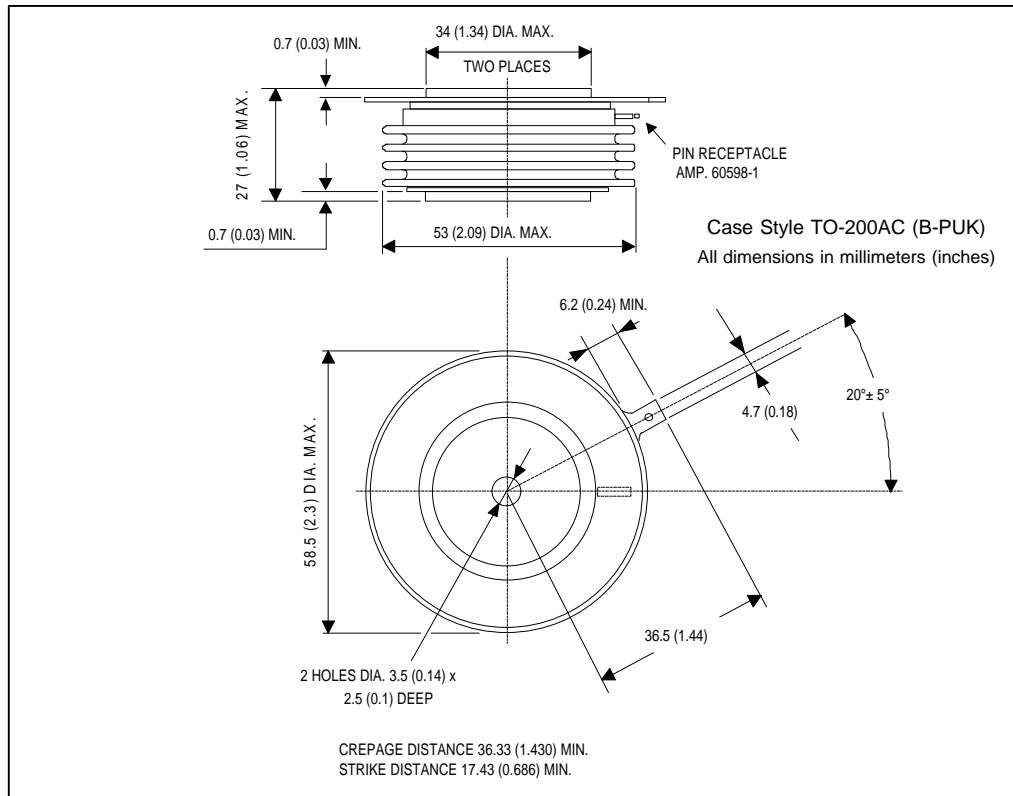


Fig. 1 - Current Ratings Characteristics

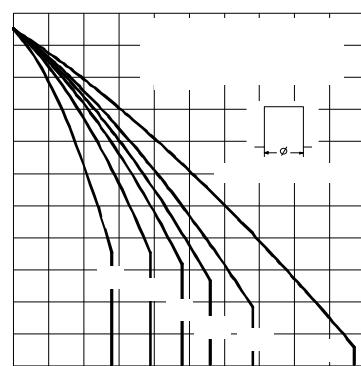


Fig. 2 - Current Ratings Characteristics